

ABSTRACT OF DISCLOSURE

Numerous embodiments of a method and apparatus for a sacrificial annealing layer are disclosed. In one embodiment, a method of forming a sacrificial annealing layer for a semiconductor device comprises forming one or more sacrificial layers on at least a portion of the top surface of a semiconductor device, annealing at least a portion of the device, and removing a substantial portion of the one or more sacrificial layers, where the removing results in no substantial physical alterations to the device.